

Silicon PNP Power Transistors

2SA1261

DESCRIPTION

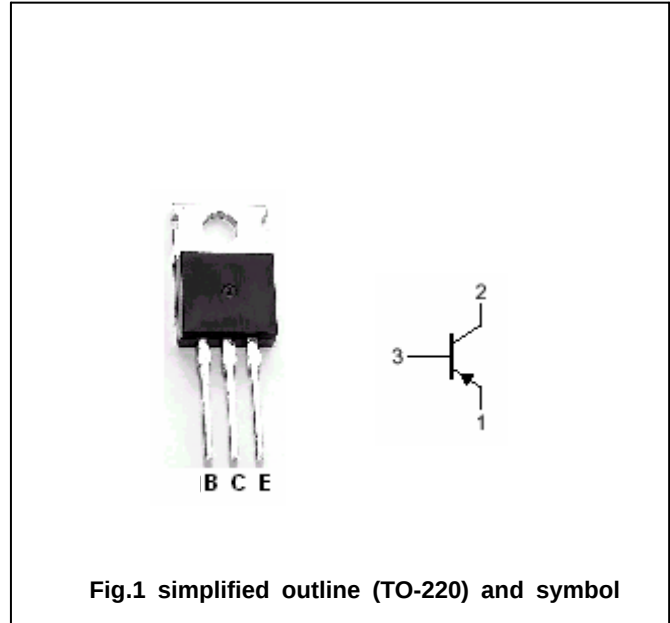
- With TO-220 package
- High switching speed
- Low collector saturation voltage
- Complement to type 2SC3157

APPLICATIONS

- For high voltage ,high speed and power switching applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base

ABSOLUTE MAXIMUM RATINGS ($T_C=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-100	V
V_{CEO}	Collector-emitter voltage	Open base	-100	V
V_{EBO}	Emitter-base voltage	Open collector	-7	V
I_C	Collector current		-10	A
I_{CM}	Collector current-Peak		-20	A
I_B	Base current		-3.5	A
P_T	Total power dissipation	$T_a=25^{\circ}\text{C}$	1.5	W
		$T_C=25^{\circ}\text{C}$	60	
T_j	Junction temperature		150	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-55~150	$^{\circ}\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =-5A; I _{B1} =-0.5A; L=1mH	-100			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =-5A; I _B =-0.5A			-0.6	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C =-5A; I _B =-0.5A			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-100V; I _E =0			-0.01	mA
I _{CEX}	Collector cut-off current	V _{CE} =-100V; V _{BE} =-1.5V T _a =125°C			-0.01 -1.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-0.01	mA
h _{FE-1}	DC current gain	I _C =-0.5A; V _{CE} =-5V	40		200	
h _{FE-2}	DC current gain	I _C =-3A; V _{CE} =-5V	40		200	
h _{FE-3}	DC current gain	I _C =-5A; V _{CE} =-5V	20			

Switching times

t _{on}	Turn-on time	I _C =-5A; I _{B1} =-I _{B2} =-0.5A, R _L =10Ω; V _{CC} =-50V			0.5	μs
t _s	Storage time				1.5	μs
t _f	Fall time				0.5	μs

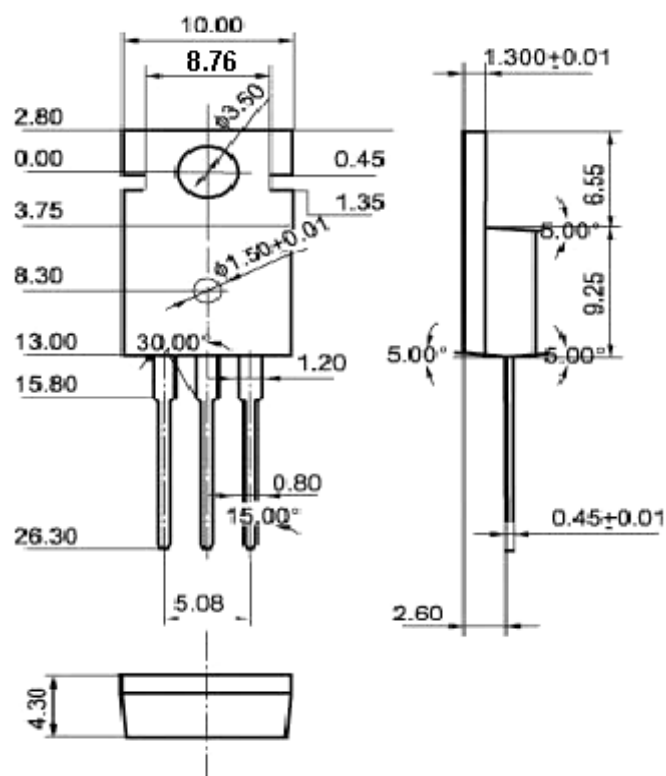
h_{FE-2} classifications

M	L	K
40-80	60-120	100-200

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PACKAGE OUTLINE

Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)